AMENDMENTS TO THE CLAIMS:

Please cancel claims 1-5, 7-18, and 20, without prejudice or disclaimer of the subject matter thereof. This listing of claims will replace all prior versions and listings of claims in the application:

1. - 5. (Canceled)

6. (Original) A semiconductor device having a lateral high-breakdown-voltage transistor comprising:

a first-conductivity-type semiconductor layer;

a second-conductivity-type source region formed in the semiconductor layer;

a second-conductivity-type drain region formed in or outside the semiconductor layer, separated from the source region;

a gate electrode formed above the semiconductor layer between the drain region and the source region, insulated from the semiconductor layer;

a second-conductivity-type drain contact region formed in the drain region and having a higher impurity concentration than the drain region;

a drain wiring electrically connected to the drain region via the drain contact region;

a first-conductivity-type substrate contact region formed adjacent to the source region; and

a source wiring electrically connected to the source region, and also connected to the semiconductor layer via the substrate contact region,

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a distance from a contact surface of the drain wiring and the drain contact region to an edge of the source region side of the drain contact region being 5 μm or more.

7. - 18. (Canceled)

19. (Original) The semiconductor device having the lateral high-breakdown-voltage transistor according to claim 6, further comprising a diode formed by short-circuiting the source wiring and the gate electrode.

20. (Canceled)

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